

In the Specification:

Please amend Paragraph 0072 as indicated below.

[0072] In a modification of the embodiment of FIG. 5 for 20V breakdown instead of 25V, the trench depth is 1.3 microns and the body and source depths remained unchanged. The drift region doping density increases from 10^{16} cm⁻³ adjacent to the body region to 10^{18} cm⁻³ adjacent to the drain region. In this structure, the field plate oxide 44 thickness is the same as the gate oxide 42 thickness.

In the Title:

Please amend the title of the invention as indicated below.

TRENCH INSULATED GATE FIELD EFFECT TRANSISTOR HAVING A
FIELD PLATE ELECTRODE